

Claims

1-24. (Canceled)

25. (Currently Amended) A method for fabricating a semiconductor circuit module as recited in claim 37, the method comprising:

providing the circuit devices [~~each having a contact area on a front side thereof~~];
applying [[a]] the patterned connection layer to a transfer substrate;
applying the front sides of the circuit devices to the patterned connection layer;
applying [[a]] the filler between the circuit devices;
removing the transfer substrate; and
applying [[an]] the electrical connection device to connect the circuit devices.

26. (Previously Presented) The method according to claim 25, further comprising applying a protection layer at least partially covering the electrical connection device.

27. (Previously Presented) The method according to claim 26, further comprising providing a second electrical connection device in a region not covered by the protection layer.

28. (Previously Presented) The method according to claim 25, wherein applying the patterned connection layer comprises printing the patterned connection layer on the transfer substrate.

29. (Previously Presented) The method according to claim 25, further comprising arranging said circuit devices on said patterned connection layer, such that the contact areas of said circuit devices are not located on said patterned connection layer.

30. (Previously Presented) The method according to claim 25, further comprising curing said patterned connection layer after applying said circuit devices.

31. **(Previously Presented)** The method according to claim 25, further comprising providing an encapsulation layer on backsides of said circuit devices.
32. **(Previously Presented)** The method according to claim 25, wherein applying the filler comprises selecting a process from the group consisting of casting and printing.
33. **(Previously Presented)** The method according to claim 31, wherein applying the encapsulation layer comprises selecting a process from the group consisting of casting and printing.
34. **(Previously Presented)** The method according to claim 25, further comprising curing said filler before removing said transfer substrate.
35. **(Previously Presented)** The method according to claim 31, further comprising curing said encapsulation layer before removing said transfer substrate.
36. **(Previously Presented)** The method according to claim 25, further comprising providing a conductive layer, providing an insulating layer separating the electrical connection device from the conductive layer, and providing an electrical connection between said conductive layer and said electrical connection device.
37. **(Previously Presented)** A semiconductor circuit module comprising circuit devices, each having a contact area on a front side thereof, a patterned connection layer connected to the front sides of the circuit devices, a filler between the circuit devices, and an electrical connection device connecting the circuit devices.

38. (Currently Amended) The semiconductor circuit module of claim 37, further comprising

a protection ~~[[device]]~~ layer covering at least part of the electrical connection device.

39. (Currently Amended) The semiconductor circuit module of claim 37, further comprising

a second electrical connection device in a region not covered by the protection ~~[[device]]~~ layer.

40. (Previously Presented) The semiconductor circuit module of claim 37, wherein said circuit devices comprise functional circuit devices.

41. (Previously Presented) The semiconductor circuit module of claim 37, further comprising

an encapsulation layer at least partially covering backsides of the circuit devices.

42. (Previously Presented) The semiconductor circuit module of claim 37, wherein said patterned connection layer comprises a dielectric material.

43. (Previously Presented) The semiconductor circuit module of claim 42, wherein said dielectric material comprises a material selected from the group consisting of a polymer, an epoxy resin, an adhesive, a silicone, and a polyamide.

44. (Previously Presented) The semiconductor circuit module of claim 37, wherein said filler comprises a curable insulator.

45. (Previously Presented) The semiconductor circuit module of claim 44, wherein said curable insulator comprises a material selected from the group consisting of a polymer, an adhesive, and a silicone.

46. **(Previously Presented)** The semiconductor circuit module of claim 41, wherein said filler layer and said encapsulation layer are the same material.
47. **(Previously Presented)** The semiconductor circuit module of claim 37, further comprising
a conductive layer,
an insulating layer separating said conductive layer from said electrical connection device, and
an electrical connection connecting said conductive layer to said electrical connection device.
48. **(Previously Presented)** The semiconductor circuit module of claim 38, further comprising
a non-conductive passivation layer on said protection device.
49. **(Previously Presented)** A stack comprising
a first circuit module as recited in claim 38,
a conductive passage, and
a second circuit module as recited in claim 38, said second circuit module being connected to the first circuit module by a conductive adhesive.
50. **(Previously Presented)** The semiconductor circuit module of claim 40, wherein said second electrical connection device comprises an edge connector.
51. **(Previously Presented)** The semiconductor circuit module of claim 40, wherein said second electrical connection device comprises a soldering pad in electrical communication with a solder ball.
52. **(Previously Presented)** The semiconductor circuit module of claim 38, wherein said semiconductor circuit module has a thickness less than 200 μm .